

CMOS Shunt-Peaked Amplifier:

Spec-Driven Design, LD Sweep, and Gain/BW/Power Across PVT Corner Analysis

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Project Overview

In this project, I designed and verified a CMOS shunt-peaked amplifier in Cadence (Spectre / ADE XL) to meet gain-peaking, bandwidth, and power targets under process/voltage/temperature variation. The testbench used $VDD = 1.0\text{ V}$, $VinDC = 700\text{ mV}$, and a small-signal input of $amp = 100\text{ mV}$ ($\approx 200\text{ mVpp}$). I applied shunt peaking by tuning the load inductor to $LD = 16.2\text{ nH}$ with $CL = 1.6\text{ pF}$ and sized the device using $nfinger = 4$ and $Multi = 20$. From AC analysis, the amplifier achieved a DC (low frequency) gain $\approx 12.45\text{ dB}$ ($\sim 4.19\text{ V/V}$) and produced the intended peaking behavior near $\sim 1\text{ GHz}$ after LD tuning. I also verified robustness across PVT corners by overlaying AC responses and recording gain at markers (100.52 MHz and $\sim 992.99\text{ MHz}$), where the corner results span approximately 4.47 to +3.41 dB (at 100.52 MHz) and -1.43 to +6.41 dB (at $\sim 992.99\text{ MHz}$). Finally, the DC operating point confirmed bias and power consistency (e.g., $Id \approx 1.296\text{ mA}$, $Vout \approx 0.820\text{ V}$, and $P \approx 1.27\text{ mW}$), reinforcing the trade-offs between LD, device sizing ($nfinger/Multi$), and frequency response.

Project at a Glance

- Tool: Cadence Virtuoso / Spectre / ADE XL
- Supply: $VDD = 1.0\text{ V}$
- Bias: $VinDC = 700\text{ mV}$
- Input swing (verification): $amp = 100\text{ mV}$ ($\approx 200\text{ mVpp}$)
- Shunt-peaking network: $LD = 16.2\text{ nH}$, $CL = 1.6\text{ pF}$
- Device sizing: $nfinger = 4$, $Multi = 20$
- Key operating point: $Vout \approx 0.820\text{ V}$, $Id \approx 1.296\text{ mA}$, $P \approx 1.27\text{ mW}$
- Key AC result: DC gain $\approx 12.45\text{ dB}$ ($\sim 4.19\text{ V/V}$), peaking near $\sim 1\text{ GHz}$

Design Approach

A shunt-peaked load was used to intentionally shape the amplifier's frequency response by introducing controlled peaking and improving high-frequency behavior compared to a purely resistive load. The primary tuning knob was L_D , which shifts the peaking frequency and changes the amount of peaking; C_L and device sizing (nfinger/Multi) set the parasitic and loading conditions that determine how strong the effect becomes. I first selected a baseline operating point (bias and sizing) that produced a reasonable DC gain and power dissipation. Next, I tuned **LD** to place the gain peaking near **~1 GHz**, and then verified the final design with sweeps and PVT corners to quantify robustness and worst-case variation.

Simulation Plan (What I Ran)

1. **DC Operating Point (op):** Confirm bias, output voltage, supply current, and DC power.
2. **AC (Typical):** Plot gain $A_v(f)$ versus frequency and extract DC gain and gain at key frequencies.
3. **LD Sweep (AC):** Sweep L_D to show how peaking and bandwidth change with tuning and to justify the final LD value.
4. **PVT Corner Sweep (AC):** Run AC analysis across PVT corners and compare gain and bandwidth variation using consistent markers.

Metrics and How They Were Measured (ADE XL)

The following metrics were extracted consistently using ADE XL expressions:

- Gain vs frequency:

$$A_v(f) = 20 \log_{10} \left| \frac{V_{out}}{V_{in}} \right|$$

implemented using `dB20(VF("/vout")/VF("/vin"))`.

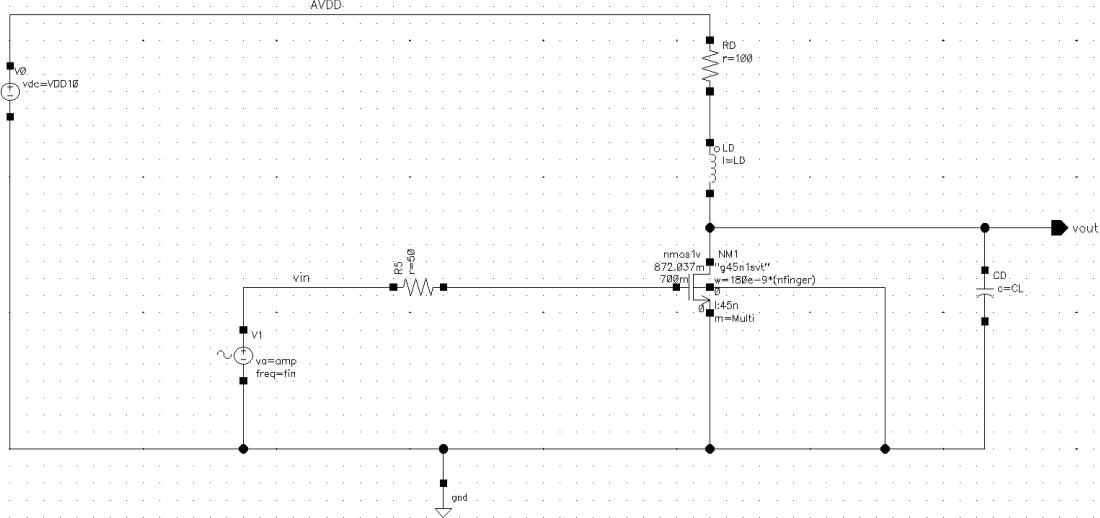
- DC gain (low-frequency gain): reported from the low-frequency region of the AC curve; measured value ≈ 12.45 dB.
- Gain at specific frequencies: evaluated at marker frequencies 100.52 MHz and ≈ 992.99 MHz (≈ 1 GHz) using `value(...)` at those points.
- 3-dB bandwidth: determined using `cross()` at the frequency where gain falls to (DC gain – 3 dB).
- DC power:

$$P_{DC} = V_{DD} \cdot I_{DD}$$

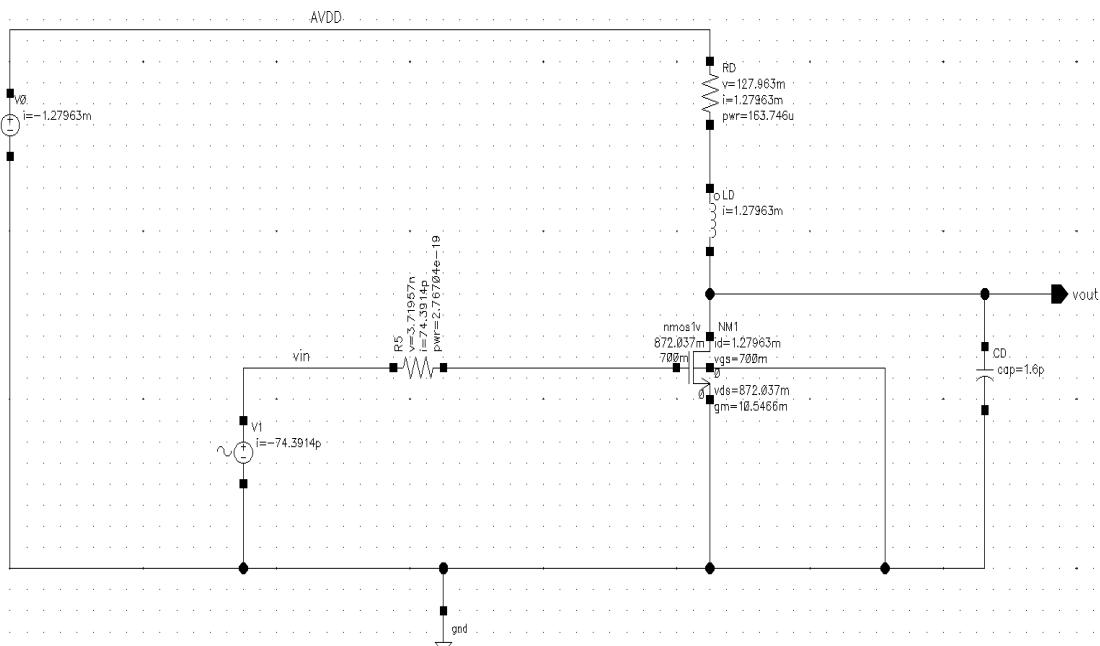
with measured values $I_D \approx 1.296$ mA and $P \approx 1.27$ mW at $VDD = 1.0$ V.

Schematics and Plots

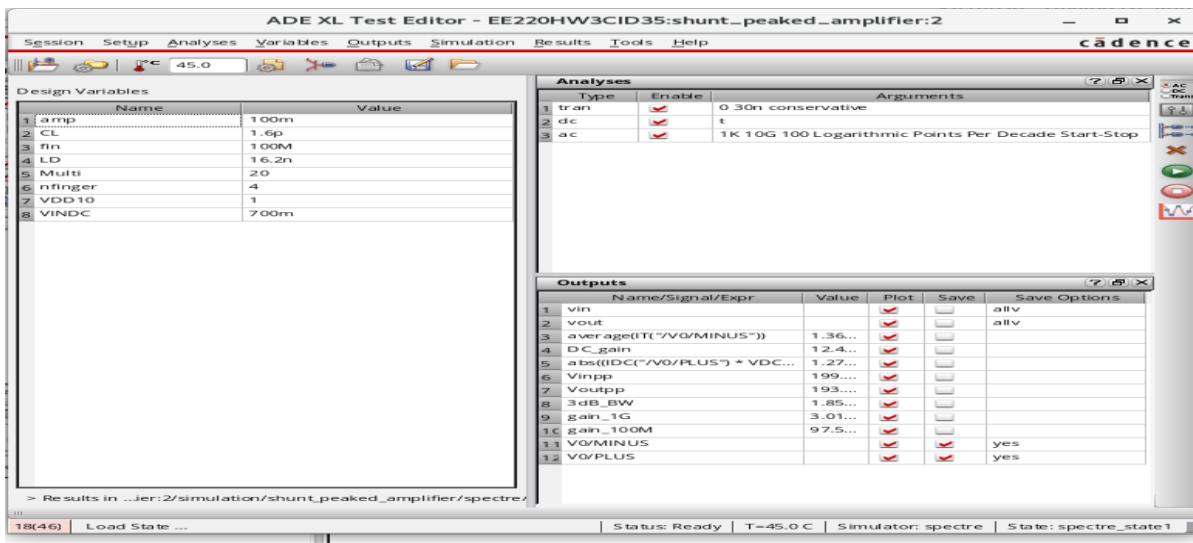
Schematic of shunt-peaked-amplifier



DC operating points



ADE XL spec.



(2) b)

$$Av = -\frac{g_m}{R_D + g_{ds}}, \quad g_{ds} = 515.5 \text{ mS} = 0.5155 \text{ S}$$

$$R_D = 100 \Omega$$

From DC operating point $V_{ds} = 870.497 \text{ mV}$, $I_d = 1.27263 \text{ mA}$

$$\Rightarrow Y_{RD} + g_{ds} = \frac{1}{100} + 0.5155 = 0.01 + 0.5155 = 0.5255 \text{ mS}$$

$$Av = -\frac{1.27263}{0.5255} \approx -20.07 \leftarrow \text{Small signal gain from DC OP point}$$

DC Gain = 12.4445 dB
convert to linear gain $Av^{\text{AC}} = 10^{(\frac{12.4445}{20})} \approx 4.19$

\Rightarrow Transient Simulation Gain $V_{in,PP} = 219.946 \text{ mV} - 579 \text{ mV} \approx 200 \text{ mV}$
 $V_{out,PP} = 958 \text{ mV} - 758 \text{ mV} \approx 200 \text{ mV}$

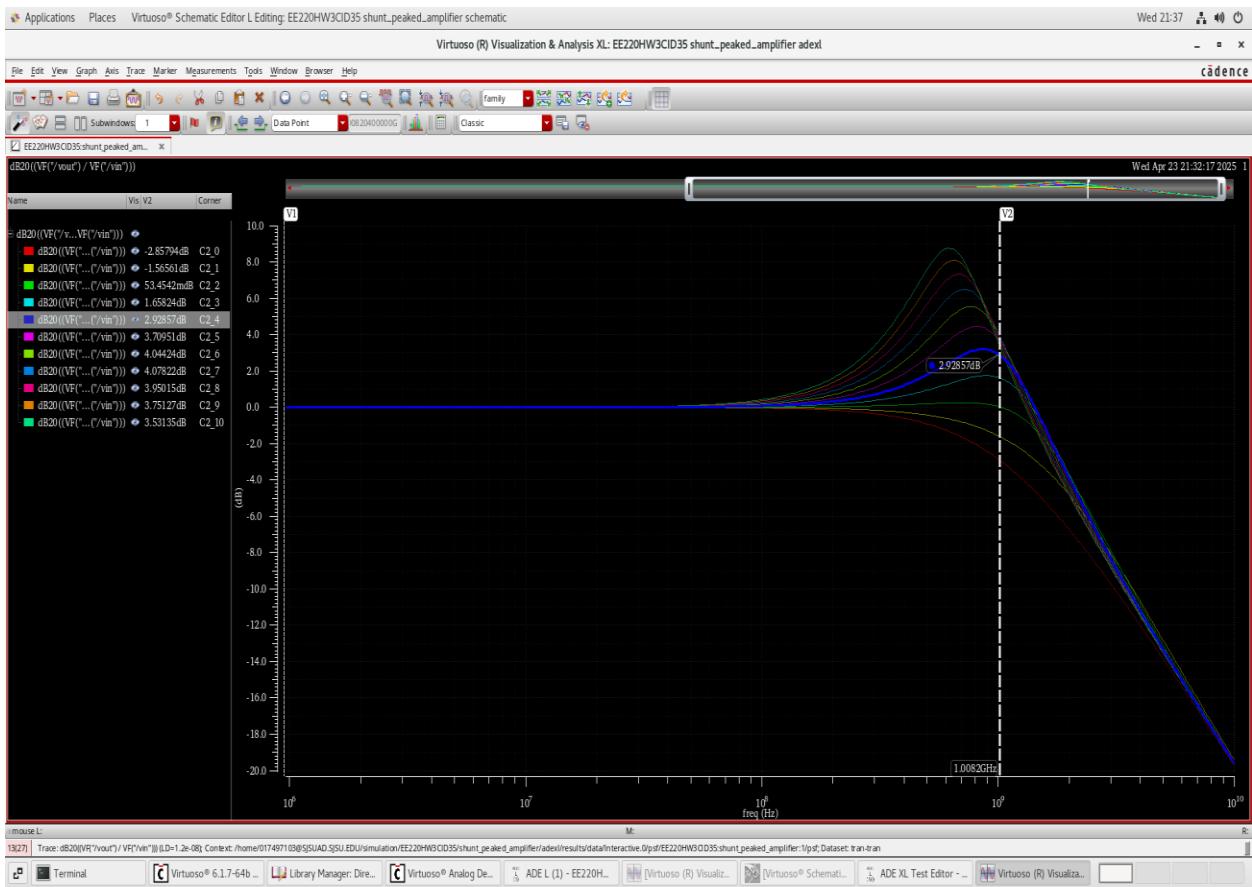
so, $A^{\text{Transient}} = \frac{V_{out,PP}}{V_{in,PP}} = \frac{200 \text{ mV}}{200 \text{ mV}} = 1.00$

$\text{In dB } 20 \log_{10}(1.00) = 0 \text{ dB}$

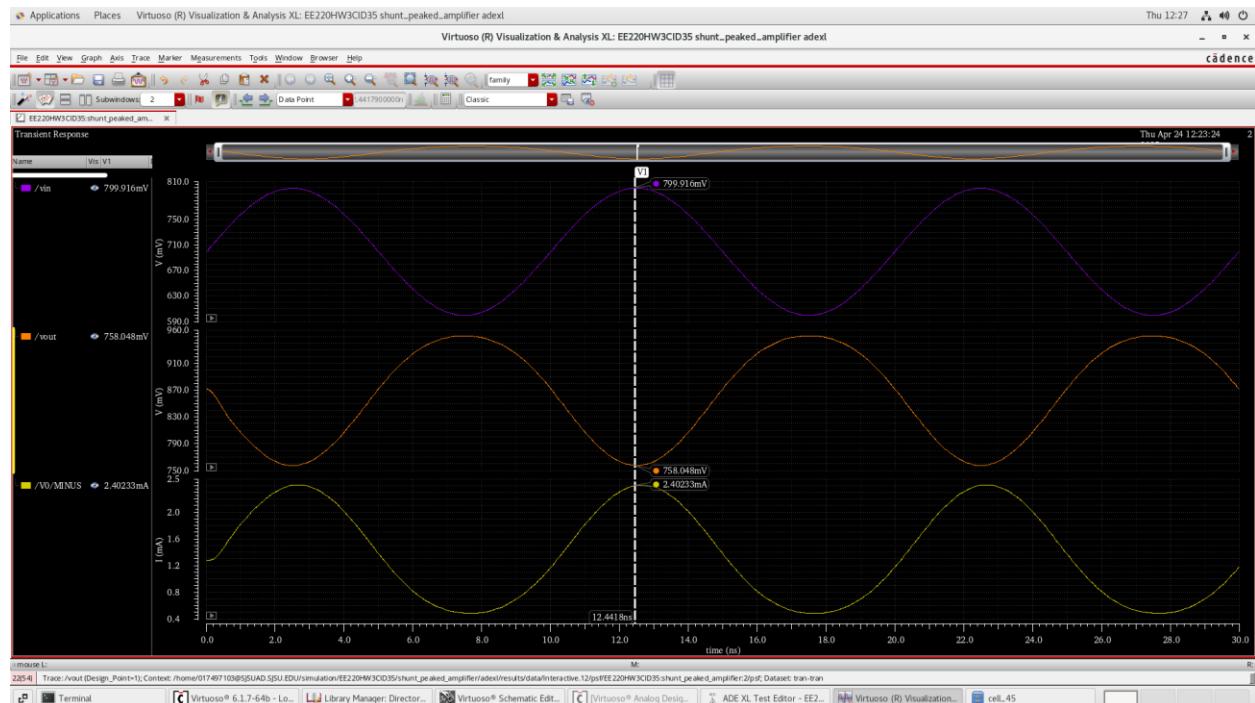
To analyze the amplifier's performance, I calculated the small-signal gain using three different methods: DC operating point, AC analysis, and transient simulation. From the DC operating point results, I used formula Av . The AC simulation result at 1 Hz yielded a gain of +12.45dB, which translates to a linear gain of about 4.19. In contrast, the transient simulation (based on the peak-to-peak input and output voltages of approximately 200 mV each) showed a gain of 1.0, or 0dB. This discrepancy can be explained by several factors. The DC small-signal model assumes ideal linear operation with no parasitics, which overestimates gain. The AC analysis includes real circuit effects such as output loading and parasitic capacitances, giving a more accurate small-signal response. The transient result reflects the actual time-domain behavior, including large-signal effects like output swing limitations, nonlinearity, and dynamic response, which can significantly reduce gain under real signal conditions.

This comparison highlights the importance of considering all simulation types to evaluate amplifier performance accurately.

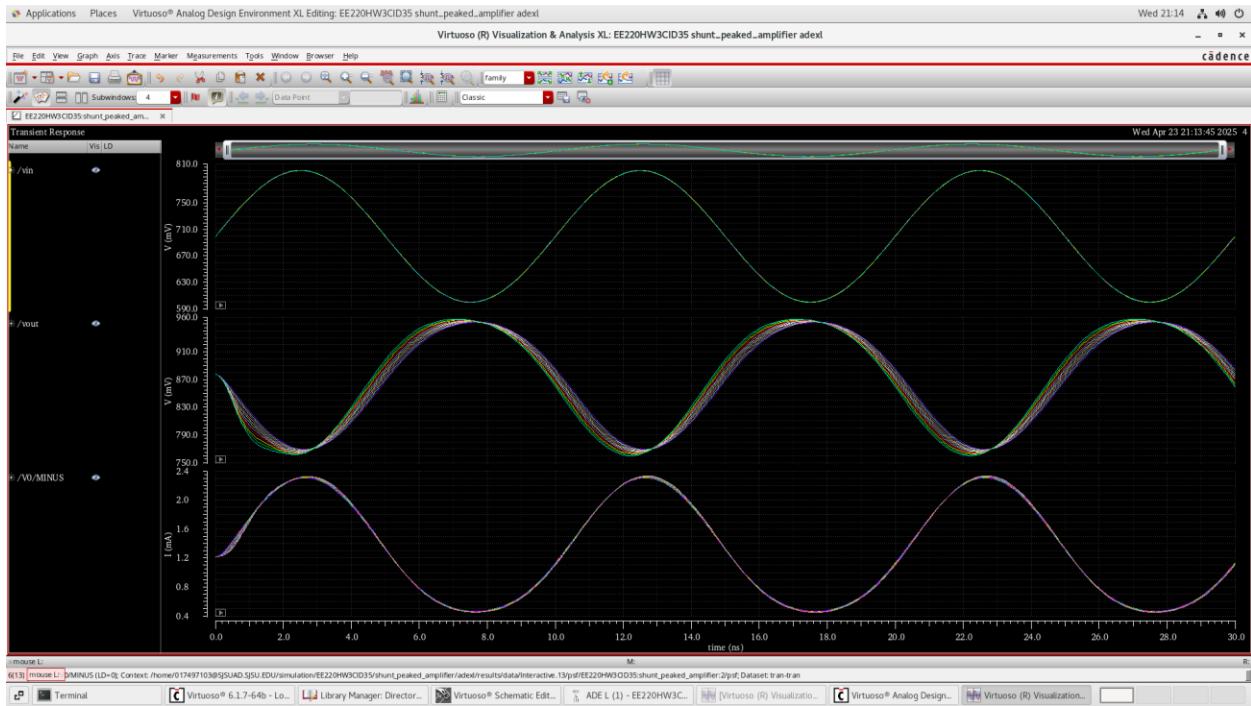
AC Response vs. LD



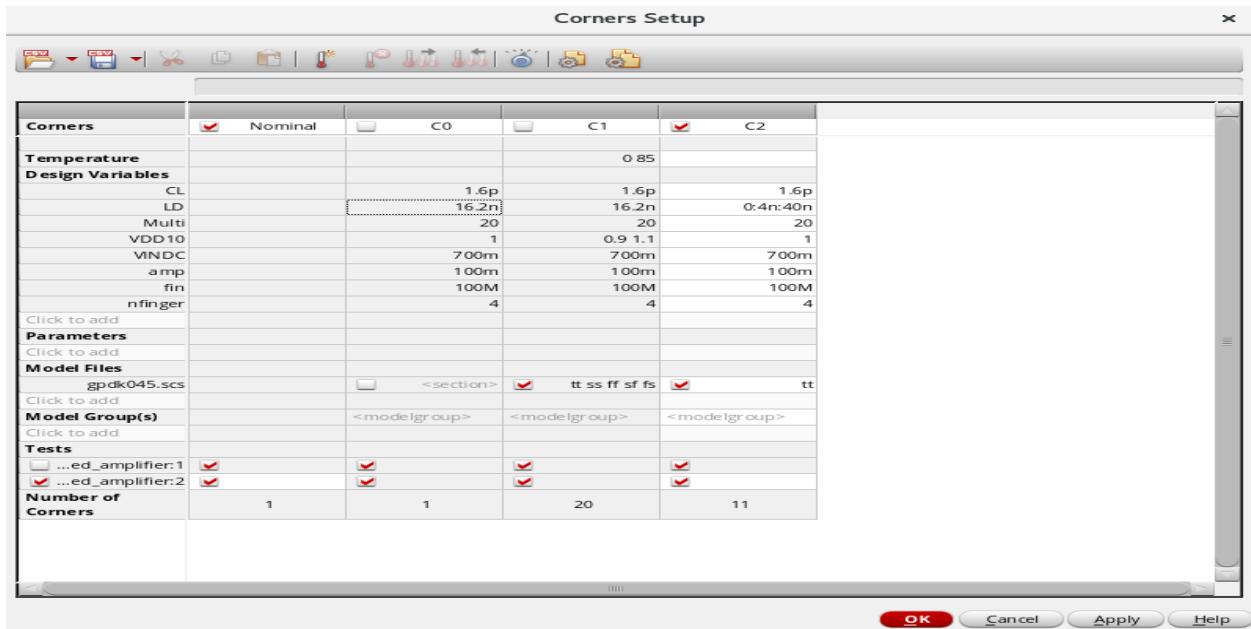
Typical Transient Response



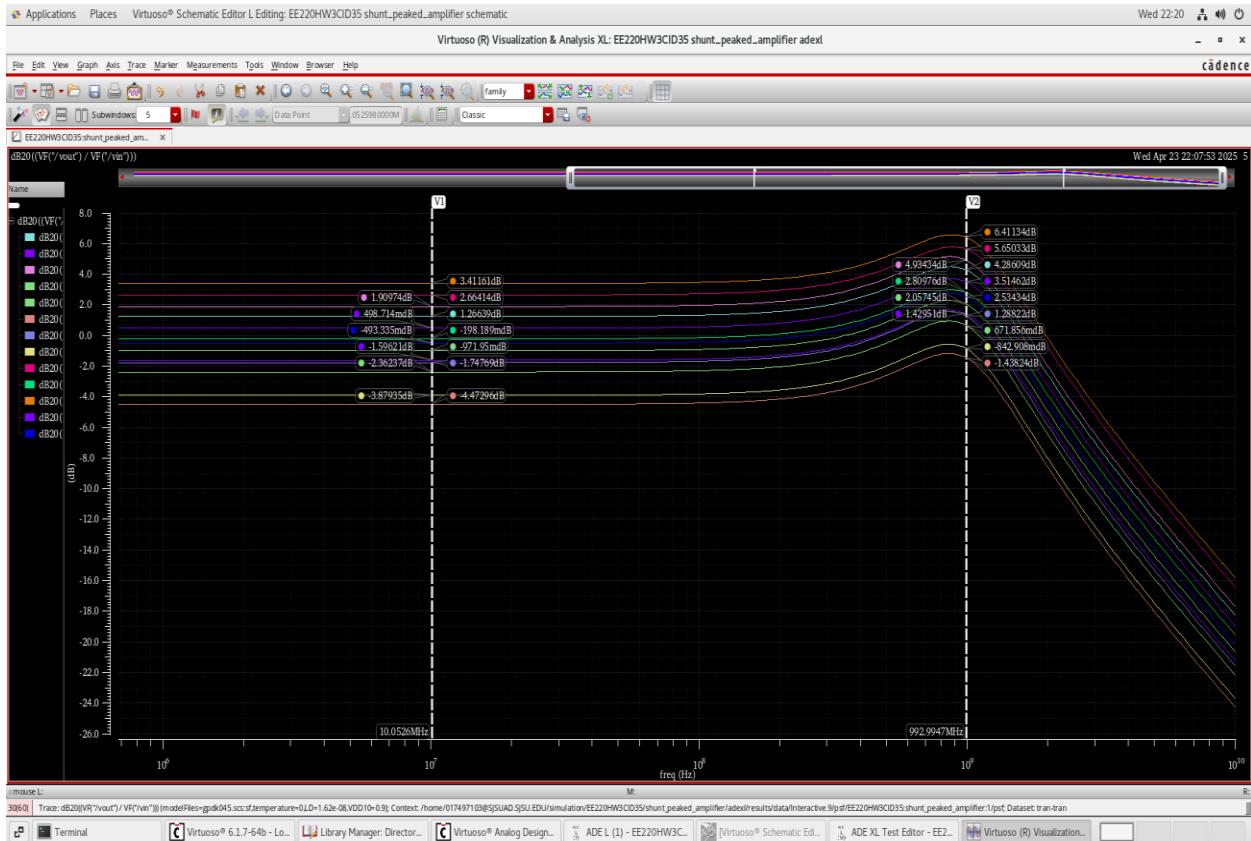
Typical Transient Response with LD sweep



PVT corner setup similar



and Here is the AC Response with LD sweep simulation below



Results Summary (Typical + Corners)

Typical (Nominal) Operating Point

- $V_{out} \approx 0.820 \text{ V}$
- $I_d \approx 1.296 \text{ mA}$
- $P \approx 1.27 \text{ mW}$
- DC gain $\approx 12.45 \text{ dB}$ ($\sim 4.19 \text{ V/V}$)
- Peaking behavior: tuned near $\sim 1 \text{ GHz}$ using $L_D = 16.2 \text{ nH}$ and $C_L = 1.6 \text{ pF}$

Corner Sensitivity (Marker-Based Summary)

To quantify PVT variation, I compared gain values at two marker frequencies: 100.52 MHz and $\sim 992.99 \text{ MHz}$. The corner sweep showed the following gain spread (relative to typical):

- At 100.52 MHz: approximately -4.47 to +3.41 dB variation across corners.
- At ~992.99 MHz: approximately -1.43 to +6.41 dB variation across corners.

(Note: exact corner names TT/SS/FF and conditions are recorded in the plotted corner overlays; the ranges above summarize worst-case behavior observed from the marker readouts.)

Conclusion

In this project, I designed and verified a CMOS amplifier with target specifications for gain, bandwidth, and power dissipation. I simulated the design across different PVT corners to evaluate performance robustness.

The AC response showed that while gain and 3 dB bandwidth varied slightly with corner, the design consistently achieved the required 3 dB peaking at ~1 GHz with LD tuning and met power constraints under all conditions.

I learned how to set up and evaluate frequency-domain responses using dB20, compute gain at specific frequencies, and find bandwidth using the cross() function. I also practiced matching my results against target specs and debugging evaluation errors in Cadence using waveform vs point outputs.

This helped reinforce my understanding of analog simulation, signal swing behavior, and trade-offs between LD, nfinger, and Multi in amplifier tuning.